

30V N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI®

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C		
30V	4.4mΩ @ V _{GS} = 10V	17.6A		
	$5.5 \text{m}\Omega$ @ $V_{GS} = 4.5 \text{V}$	16.1A		

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

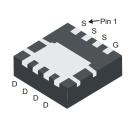
Features and Benefits

- Low R_{DS(ON)} Ensures on-state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies only 33% of the board area occupied by SO-8 enabling smaller end products
- 100% Unclamped Inductive Switch (UIS) test in production
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

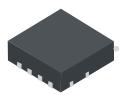
Mechanical Data

- Case: POWERDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)

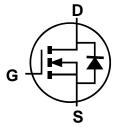
POWERDI®3333-8



Bottom View



Top View



Equivalent Circuit

Ordering Information (Note 4)

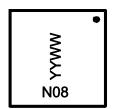
Part Number	Case	Packaging
DMN3008SFG-7	POWERDI®3333-8	2,000/Tape & Reel
DMN3008SFG-13	POWERDI®3333-8	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

POWERDI®3333-8



N08= Product Type Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 13 = 2013) WW = Week Code (01 ~ 53)



Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V_{DSS}	30	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Durin Courset (Note CVV - 40V	Steady State	T _A = +25°C T _A = +70°C	I _D	17.6 14.1	А
Continuous Drain Current (Note 6) V _{GS} = 10V	t<10s	T _A = +25°C T _A = +70°C	I _D	23.0 18.4	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	80	Α		
Maximum Continuous Body Diode Forward Current (I _S	2	Α		
Avalanche Current, L = 0.1mH	I _{AS}	45	Α		
Avalanche Energy, L = 0.1mH	E _{AS}	101	mJ		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Total Dawer Dissipation (Note 5)	T _A = +25°C	Г.	0.9	W	
Total Power Dissipation (Note 5)	T _A = +70°C	P_{D}	0.6		
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	134	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t < 10s	$R_{\theta JA}$	79	°C/W	
Total Power Dissipation (Note 6)	T _A = +25°C	Б	2.1	W	
Total Power Dissipation (Note 6)	$T_A = +70^{\circ}C$	P_{D}	1.3	VV	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	П	58	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t < 10s	$R_{\theta JA}$	34	°C/W	
Thermal Resistance, Junction to Case (Note 6)	R _{0JC}	6.6	°C/W		
Operating and Storage Temperature Range		$T_{J_{I}}T_{STG}$	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

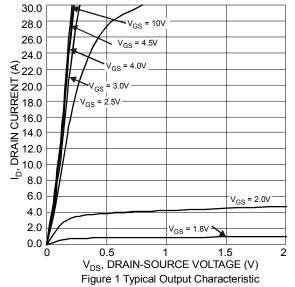
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	30		_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	10	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(th)}$	1		2.3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance			3.9	4.4	mΩ	$V_{GS} = 10V, I_D = 13.5A$	
Static Drain-Source On-Nesistance	R _{DS (ON)}		4.6	5.5	11122	$V_{GS} = 4.5V$, $I_D = 13.5A$	
Diode Forward Voltage	V_{SD}	1	0.75	1.2	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C_{iss}	_	3690	_	pF	\\ -40\\\\ -0\\	
Output Capacitance	Coss	I	530	ı	pF	V _{DS} = 10V, V _{GS} = 0V, -f = 1MHz	
Reverse Transfer Capacitance	C_{rss}	l	459	1	pF	1 - 1101112	
Gate resistance	R_g	I	0.9	ı	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz	
Total Gate Charge (V _{GS} = 4.5V)	Q_g	I	41	ı	nC		
Total Gate Charge (V _{GS} = 10V)	Q_g	I	86	1	nC	7, 04, 1, 074	
Gate-Source Charge	Q_{gs}		9.2	_	nC	$V_{DS} = 24V, I_D = 27A$	
Gate-Drain Charge	Q_{gd}	l	18.6	1	nC	7	
Turn-On Delay Time	t _{D(on)}	I	5.7	ı	ns	$V_{DD} = 15V$, $V_{GS} = 10V$, $R_{L} = 1.11\Omega$, $R_{G} = 4.7\Omega$, $I_{D} = 13.5A$	
Turn-On Rise Time	t _r	_	14.0	_	ns		
Turn-Off Delay Time	t _{D(off)}	_	63.7	_	ns		
Turn-Off Fall Time	t _f	1	28.4		ns		
Reverse Recovery Time	t _{rr}	1	19.3	_	ns	L =13 EA di/dt=100A/vs	
Reverse Recovery Charge	Qrr	-	10.7	_	nC	I _F =13.5A, di/dt=100A/μs	

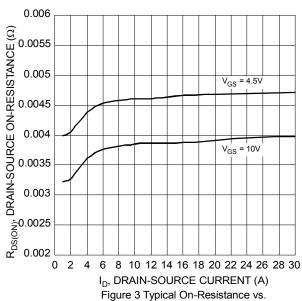
 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. Notes:

^{7.} Short duration pulse test used to minimize self-heating effect.

^{8.} Guaranteed by design. Not subject to product testing.







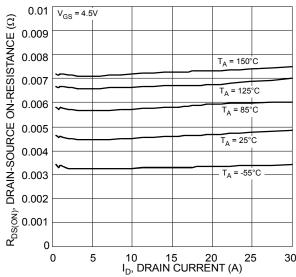
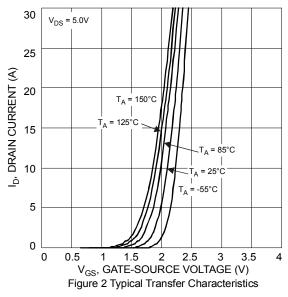
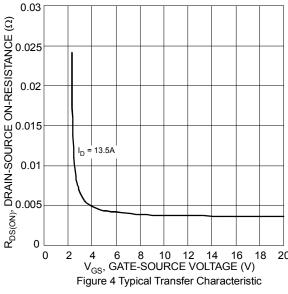
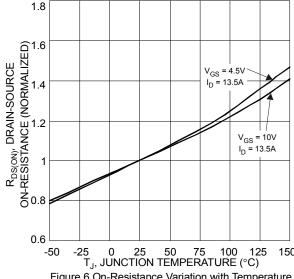


Figure 5 Typical On-Resistance vs.
Drain Current and Temperature
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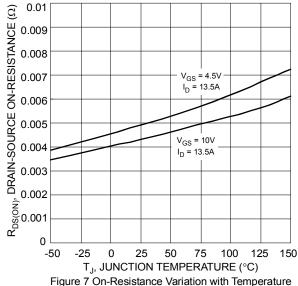
Drain Current and Gate Voltage

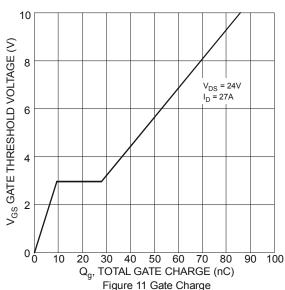


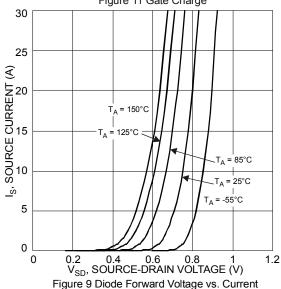


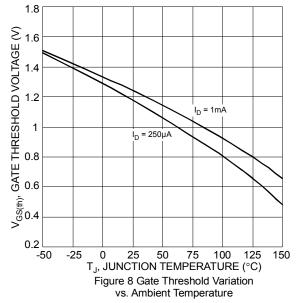


DMN3008SFG









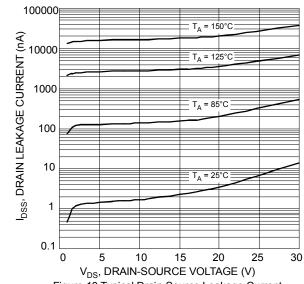
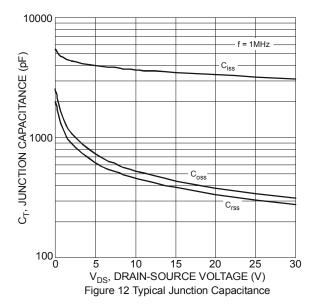
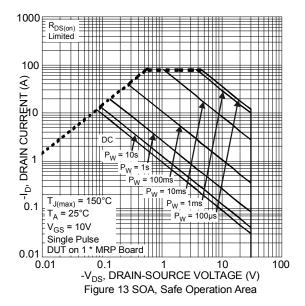
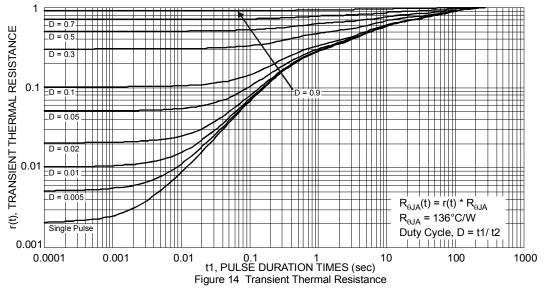


Figure 10 Typical Drain-Source Leakage Current vs. Voltage







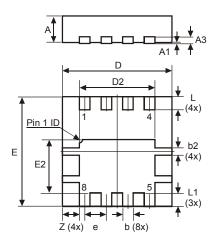




Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

POWERDI®3333-8

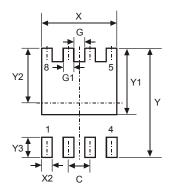


POWERDI®3333-8					
Dim	Min	Max	Тур		
D	3.25	3.35	3.30		
Е	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
E2	1.56	1.66	1.61		
Α	0.75	0.85	0.80		
A1	0	0.05	0.02		
A3	_	_	0.203		
b	0.27	0.37	0.32		
b2	_	-	0.20		
L	0.35	0.45	0.40		
L1	_	_	0.39		
е	_	_	0.65		
Z	_	_	0.515		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

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Dimensions	Value (in mm)			
С	0.650			
G	0.230			
G1	0.420			
Y	3.700			
Y1	2.250			
Y2	1.850			
Y3	0.700			
Х	2.370			
X2	0.420			



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